NSN 5962-01-108-8797

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View Online at https://aerobasegroup.com/nsn/5962-01-108-8797

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Body Length:
1.290 inches
Body Width:
Between 0.500 inches and 0.610 inches
Body Height:
Between 0.150 inches and 0.205 inches
Maximum Power Dissipation Rating:
1.4 watts
Operating Tempurature Range:
-55.0/+125.0 degrees celsius
Storage Tempurature Range:
-65.0/+150.0 degrees celsius
Features Provided:
Hermetically sealed and monolithic and positive outputs and bipolar and schottky and w/enable and 3-state output
Inclosure Material:
Ceramic and glass
Inclosure Configuration:
Dual-in-line
Output Logic Form:
Transistor-transistor logic
Input Circuit Pattern:
14 input
Case Outline Source And Designator:
D-3 mil-m-38510
Terminal Surface Treatment:
Solder
Voltage Rating And Type Per Characteristic:
5.5 volts power source
Time Rating Per Chacteristic:
125.00 nanoseconds propagation delay time, low to high level output and 125.00 nanoseconds propagation delay time, high to low level
output
Memory Device Type:
Rom
Memory Capacity:
Unknown
Test Data Document:
81349-mil-m-38510 specification (includes engineering type bulletins, brochures, etc., that reflect specification type data in specification

format; excludes commercial catalogs, industry directories, and similar trade publications, reflecting general type data on certain

environmental and performance requirements and test conditions that are shown as "typical", "average", "", etc.). **Terminal Type And Quantity:**

24 printed circuit

Specification Data:

81349-mil-m-38510/209 government specification

Shelf Life:

N/a

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Demilitarization:

Yes - demil/mli

Fiig:

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